

L Number	Hits	Search Text	DB	Time stamp
1	1712	ozone near5 (barrier stripping resistant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:26
2	30061	349\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:26
3	1	(ozone near5 (barrier stripping resistant)) and 349\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:27
4	50845	tft (thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:31
5	398453	ito (indium adj tin adj oxide) (electrically adj conductive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:32
6	910993	aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:32
7	395263	titanium tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:33
8	167	(tft (thin adj film adj transistor)) same (ito (indium adj tin adj oxide) (electrically adj conductive)) same aluminum same (titanium tantalum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:33
9	47	349\$.ccls. and ((tft (thin adj film adj transistor)) same (ito (indium adj tin adj oxide) (electrically adj conductive)) same aluminum same (titanium tantalum))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:56
10	403	ozone near10 (titanium tantalum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:56
11	0	349\$.ccls. and (ozone near10 (titanium tantalum))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:56
12	195862	257\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:57
13	48	(ozone near10 (titanium tantalum)) and 257\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:59
14	12	(ozone near5 (barrier stripping resistant)) near10 (titanium tantalum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:59